



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent of:

YAN et al.

Patent No. 6,806,492 B2

Issued: October 14, 2004

For: HETEROJUNCTION ORGANIC
SEMICONDUCTOR FIELD EFFECT
TRANSISTOR (FET) WITH A GATE
INSULATION LAYER AND
MANUFACTURING PROCESS
THEREOF

Examiner: Mark V. Prenty

Confirmation No. 9240

Atty. Docket No. 33419-190319

Customer No.

26694

PATENT TRADEMARK OFFICE

Certificate
NOV 16 2004

REQUEST FOR CERTIFICATE OF CORRECTION

of Correction

Mail Stop – **OFFICE OF PUBLICATIONS**
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Applicants hereby respectfully petition for entry of the attached Certificate of Correction in the above-referenced patent. It is respectfully submitted that all of the listed corrections are of a clerical or typographical nature or are mistakes of minor character, and do not involve changes that would constitute new matter or require reexamination.

As the error originated at the United States Patent and Trademark Office, it is not believed that any fee is due. However, any required fee is hereby authorized to be charged to Deposit Account No. 22-0261.

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REMARKS

It is respectfully submitted that Figure 1 of the issued patent is not Figure 1 as filed by applicants, and has no relationship to the subject patent. Correction of the patent to insert the correct figure is respectfully requested.

Approval and entry of the Certificate of Correction are respectfully requested.

Respectfully submitted,

Date: 11/12/04



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UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO : 6,806,492 B2

ATTY DOCKET NO. : 33419-190319

DATED : October 19, 2004

INVENTOR(S) : Donghang Yan et al.

It is certified that error appears in the above-identified patent and that said Letters Patent are hereby corrected as shown below:

Please replace Figure 1 with attached Figure 1 on page 1 of the Letters Patent, and Sheet #1.

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PATENT NO. 6,806,492 B2

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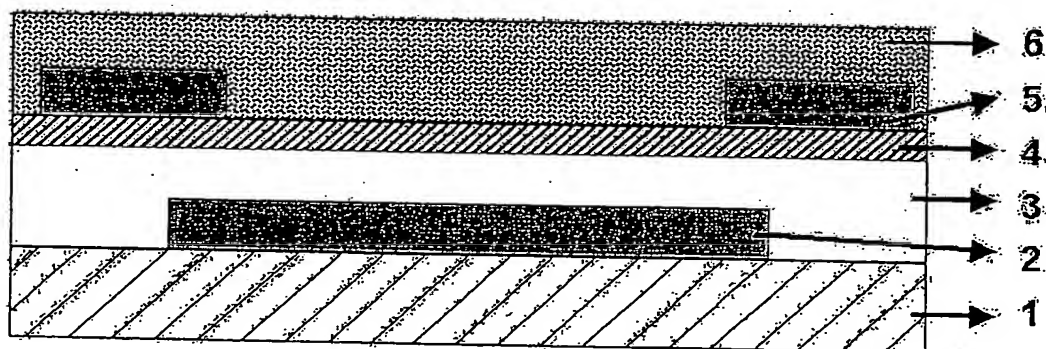


Fig.1

Inventor: Donghang YAN et al.
Title: Heterojunction Organic Semiconductor Field
Effect Transistor (FET) with a Gate Insulation
Layer and Manufacturing Process Thereof
Attorney Docket No.: 33419-190319